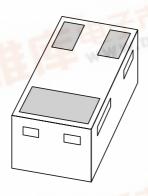
DISCRETE SEMICONDUCTORS

DATA SHEET



BC847M series NPN general purpose transistors

Product specification
Supersedes data of 2003 Jul 15







NPN general purpose transistors

BC847M series

FEATURES

- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.3 × 0.9 mm
- Power dissipation comparable to SOT23.

APPLICATIONS

- General purpose small signal DC
- Low and medium frequency AC applications
- Mobile communications, digital (still) cameras, PDAs, PCMCIA cards.

DESCRIPTION

NPN general purpose transistor in a SOT883 leadless ultra small plastic package.

PNP complement: BC857M series.

MARKING

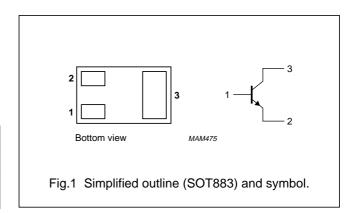
TYPE NUMBER	MARKING CODE
BC847AM	D4
BC847BM	D5
BC847CM	D6

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	45	V
I _C	collector current (DC)	100	mA
I _{CM}	peak collector current	200	mA

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



ORDERING INFORMATION

TYPE NUMBER		PACKAGE	
NAME DESCRIPTION		DESCRIPTION	VERSION
BC847AM	_	Leadless ultra small plastic package; 3 solder lands; body	SOT883
BC847BM		1.0 x 0.6 x 0.5 mm	
BC847CM			

2004 Mar 10 2

NPN general purpose transistors

BC847M series

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	50	V
V _{CEO}	collector-emitter voltage	open base	_	45	V
V _{EBO}	emitter-base voltage	open collector	_	5	V
I _C	collector current (DC)		_	100	mA
I _{CM}	peak collector current		_	200	mA
I _{BM}	peak base current		_	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C			
		note 1	_	250	mW
		note 2	_	430	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μ m copper stripline.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		
		note 1	500	K/W
		note 2	290	K/W

3

Notes

- 1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper stripline.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, mounting pad for collector 1 cm².

NPN general purpose transistors

BC847M series

CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	V _{CB} = 30 V; I _E = 0	_	15	nA
		V _{CB} = 30 V; I _E = 0; T _j = 150 °C	_	5	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0$	_	100	nA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$			
	BC847AM		110	220	
	BC847BM		200	450	
	BC847CM		420	800	
V _{BE}	base-emitter voltage	I _C = 2 mA; V _{CE} = 5 V	580	700	mV
		I _C = 10 mA; V _{CE} = 5 V	_	770	mV
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	200	mV
		I _C = 100 mA; I _B = 5 mA; note 1	_	400	mV
C _c	collector capacitance	$I_E = i_e = 0$; $V_{CB} = 10 \text{ V}$; $f = 1 \text{ MHz}$	_	1.5	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	100	_	MHz
F	noise figure	I_C = 200 μA; V_{CE} = 5 V; R_S = 2 kΩ; f = 1 kHz; B = 200 Hz	_	10	dB

Note

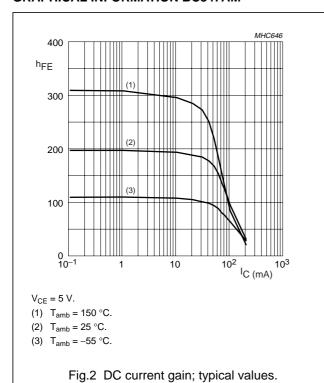
1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

NPN general purpose transistors

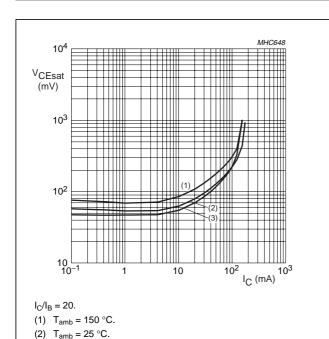
BC847M series

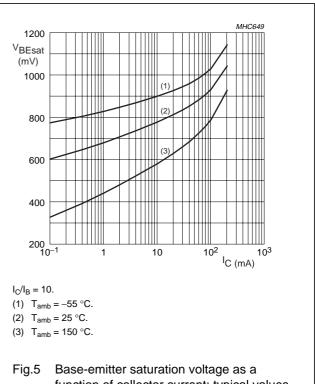
MHC647

GRAPHICAL INFORMATION BC847AM



V_{BE} (mV)
1000
800
400
400
10-1
1
10
10² |_C (mA)
10³
V_{CE} = 5 V.
(1) T_{amb} = -55 °C.
(2) T_{amb} = 25 °C.
(3) T_{amb} = 150 °C.
Fig.3 Base-emitter voltage as a function of collector current; typical values.





g.4 Collector-emitter saturation voltage as a function of collector current; typical values.

Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

5

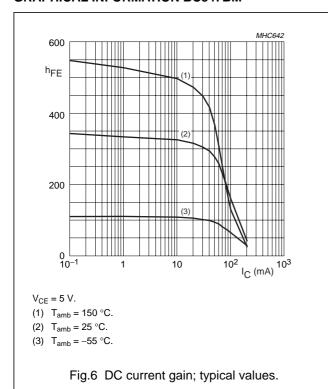
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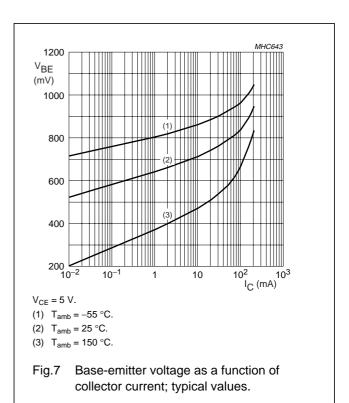
(3) $T_{amb} = -55 \, ^{\circ}C$.

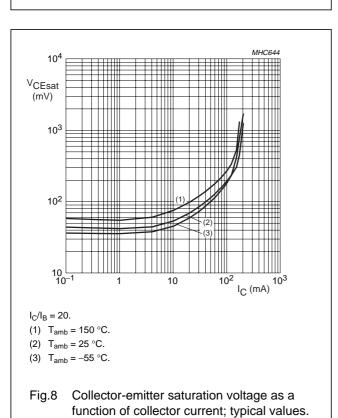
NPN general purpose transistors

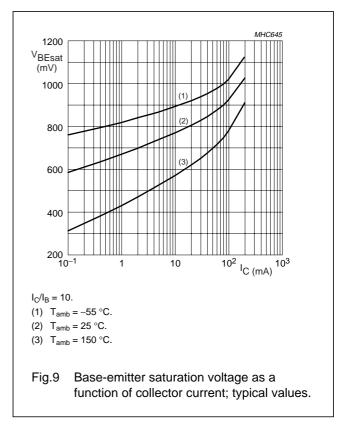
BC847M series

GRAPHICAL INFORMATION BC847BM









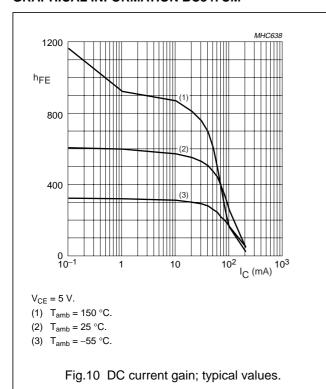
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6

NPN general purpose transistors

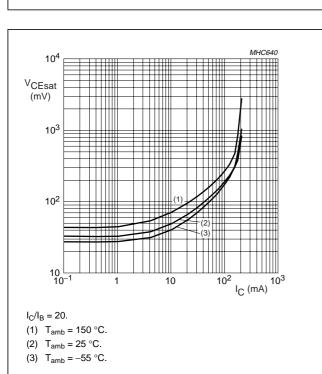
BC847M series

GRAPHICAL INFORMATION BC847CM



V_{BE} (mV)
800 $\frac{1200}{10^{-2}}$ $\frac{10^{-1}}{10^{-1}}$ $\frac{10^{-2}}{10^{-1}}$ $\frac{10^{-2}}{10^{-3}}$ $\frac{10^{-2}}{10^{-1}}$ $\frac{10^{-2}}{10^{-1}}$ $\frac{10^{-2}}{10^{-3}}$ $\frac{10^{-2$

collector current; typical values.



1200 V_{BEsat} (mV) 1000 800 600 400 200 10-1 10² I_{C (mA)} 10³ 10 $I_{\rm C}/I_{\rm B}=10.$ (1) $T_{amb} = -55 \, ^{\circ}C$. (2) $T_{amb} = 25 \, ^{\circ}C$. (3) $T_{amb} = 150 \, ^{\circ}C$. Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

7

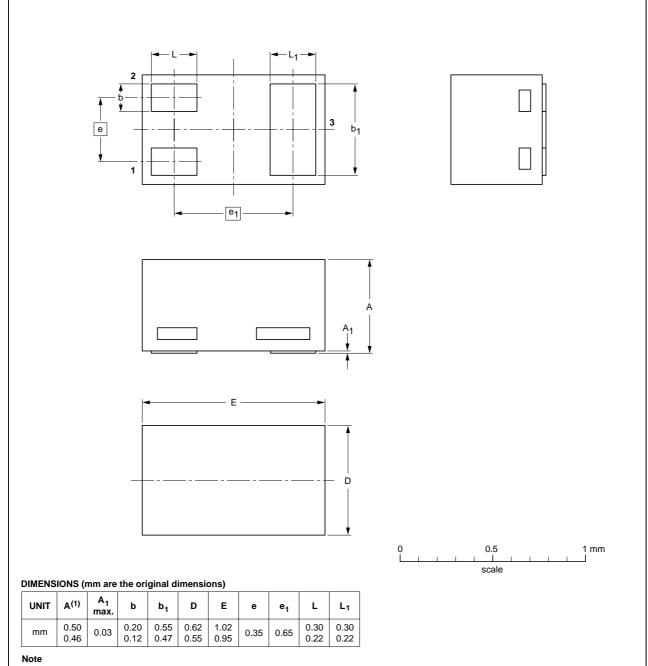
NPN general purpose transistors

BC847M series

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



1. Including plating thickness

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT883			SC-101			03-02-05 03-04-03

NPN general purpose transistors

BC847M series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
III	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

Notes

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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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2004 Mar 10 9

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SCA76

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Printed in The Netherlands

R75/02/pp10

Date of release: 2004 Mar 10

Document order number: 9397 750 12838

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